

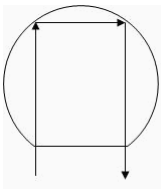
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm
	2.0	Primary Flat Length	57.50 +/- 2.50 mm
	3.0	Primary Flat Orientation	{110} +/- 1 degree
	4.0	Secondary Flat Orientation	None
	5.0	Overall Thickness	501.00 +/- 12.00 µm
	6.0	Total Thickness Variation (TTV)	<3.00µm
	7.0	Bow	<60.00µm
	8.0	Warp	<60.00µm
	9.0	Edge Chips	None
	10.0	Edge Exclusion	5mm
HandleSilicon	11.0	Handle Growth Method	CZ
	12.0	Handle Orientation	{111} +/- 0.5 degree
	13.0	Handle Thickness	400.00 +/- 10.00 µm
	14.0	Handle Doping Type	P
	15.0	Handle Dopant	Boron
	16.0	Handle Resistivity	1- 30 Ohm-cm
	17.0	Backside Finish	Polished with oxide and laser mark
BuriedOxide	18.0	Oxide Type	Thermal
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A
	20.0	Oxide formed on	Handle and/or Device Wafer
DeviceSilicon	21.0	Device Orientation	{111} +/- 0.5 degree
	22.0	Nominal Thickness	100.00 +/- 1.00 µm
	23.0	Distance to device silicon edge from wafer edge	<= 2.0mm
	24.0	Device Doping Type	P
	25.0	Device Dopant	Boron
	26.0	Device Growth Method	CZ
	27.0	Device Resistivity	0.01- 0.1 Ohm-cm
	28.0	Voids	None
	29.0	Scratches	Frontside - no scratches allowed. Backside - light handling marks
	30.0	Haze	None

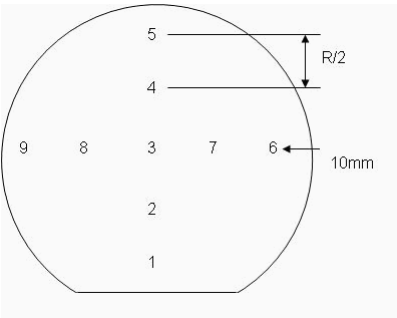
Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information